NSN 5962-01-352-1008

Memory Microcircuit - Page 1 of 2

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Body Length:

0.540 inches

Body Width:

Between 0.245 inches and 0.300 inches

Body Height:

Between 0.045 inches and 0.100 inches

Maximum Power Dissipation Rating:

600.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

5895-01-299-3419 converter, signal data

Features Provided:

Hermetically sealed and burn in and monolithic and positive outputs

Inclosure Material:

Ceramic

Inclosure Configuration:

Leadless flat pack

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

16 input

Case Outline Source And Designator:

F-9 mil-m-38510

Current Rating Per Characteristic:

105.00 milliamperes reverse current, dc absolute

Terminal Surface Treatment:

Solder

Product Name:

And-or invert gate array

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

Time Rating Per Chacteristic:

30.00 nanoseconds delay

Memory Device Type:

Pal

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 flat leads

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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